

FTP06N80A-VB Datasheet

N-Channel 800V (D-S) Super Junction Power MOSFET

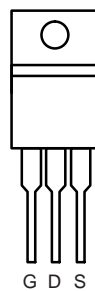
| PRODUCT SUMMARY           |                            |
|---------------------------|----------------------------|
| $V_{DS}$ (V)              | 800                        |
| $R_{DS(on)}$ ( $\Omega$ ) | $V_{GS} = 10\text{ V}$ 1.2 |
| $Q_g$ (Max.) (nC)         | 200                        |
| $Q_{gs}$ (nC)             | 24                         |
| $Q_{gd}$ (nC)             | 110                        |
| Configuration             | Single                     |

FEATURES

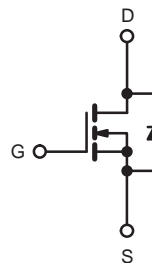
- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Isolated Central Mounting Hole
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Compliant to RoHS Directive 2002/95/EC



TO-220AB



Top View



N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted) |                                  |                                   |                  |                     |
|---|----------------------------------|-----------------------------------|------------------|---------------------|
| PARAMETER   | SYMBOL                           | LIMIT                             | UNIT             |                     |
| Drain-Source Voltage  | $V_{DS}$                         | 800                               | V                |                     |
| Gate-Source Voltage   | $V_{GS}$                         | $\pm 20$                          |                  |                     |
| Continuous Drain Current  | $V_{GS}$ at 10 V                 | $T_C = 25\text{ }^\circ\text{C}$  | 5                | A                   |
|   |                                  | $T_C = 100\text{ }^\circ\text{C}$ | 3.9              |                     |
| Pulsed Drain Current <sup>a</sup>   |                                  | $I_{DM}$                          | 21               |                     |
| Linear Derating Factor  |                                  |                                   | 1.5              | W/ $^\circ\text{C}$ |
| Single Pulse Avalanche Energy <sup>b</sup>  |                                  | $E_{AS}$                          | 770              | mJ                  |
| Repetitive Avalanche Current <sup>a</sup>   |                                  | $I_{AR}$                          | 7.8              | A                   |
| Repetitive Avalanche Energy <sup>a</sup>  |                                  | $E_{AR}$                          | 19               | mJ                  |
| Maximum Power Dissipation   | $T_C = 25\text{ }^\circ\text{C}$ | $P_D$                             | 190              | W                   |
| Peak Diode Recovery dV/dt <sup>c</sup>  |                                  | dV/dt                             | 2.0              | V/ns                |
| Operating Junction and Storage Temperature Range                                      |                                  | $T_J, T_{stg}$                    | - 55 to + 150    | $^\circ\text{C}$    |
| Soldering Recommendations (Peak Temperature)  | for 10 s                         |                                   | 300 <sup>d</sup> |                     |
| Mounting Torque   | 6-32 or M3 screw                 |                                   | 10               | lbf · in            |
|   |                                  |                                   | 1.1              | N · m               |



Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50\text{ V}$ , starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 23\text{ mH}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 7.8\text{ A}$  (see fig. 12).
- $I_{SD} \leq 7.8\text{ A}$ ,  $dI/dt \leq 140\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq 600\text{ V}$ ,  $T_J \leq 150\text{ }^\circ\text{C}$ .
- 1.6 mm from case.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

| THERMAL RESISTANCE RATINGS          |            |      |      |      |
|-------------------------------------|------------|------|------|------|
| PARAMETER                           | SYMBOL     | TYP. | MAX. | UNIT |
| Maximum Junction-to-Ambient         | $R_{thJA}$ | -    | 40   | °C/W |
| Case-to-Sink, Flat, Greased Surface | $R_{thCS}$ | 0.24 | -    |      |
| Maximum Junction-to-Case (Drain)    | $R_{thJC}$ | -    | 0.65 |      |

**SPECIFICATIONS** ( $T_J = 25\text{ °C}$ , unless otherwise noted)

| PARAMETER                                      | SYMBOL              | TEST CONDITIONS  | MIN. | TYP. | MAX.      | UNIT          |
|--|---------------------|--|------|------|-----------|---------------|
| <b>Static</b>                                  |                     |  |      |      |           |               |
| Drain-Source Breakdown Voltage                 | $V_{DS}$            | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$  | 800  | -    | -         | V             |
| $V_{DS}$ Temperature Coefficient               | $\Delta V_{DS}/T_J$ | Reference to $25\text{ °C}$ , $I_D = 1\text{ mA}$  | -    | 0.98 | -         | V/°C          |
| Gate-Source Threshold Voltage                  | $V_{GS(th)}$        | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$  | 2.0  | -    | 4.0       | V             |
| Gate-Source Leakage                            | $I_{GSS}$           | $V_{GS} = \pm 20\text{ V}$   | -    | -    | $\pm 100$ | nA            |
| Zero Gate Voltage Drain Current                | $I_{DSS}$           | $V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$   | -    | -    | 100       | $\mu\text{A}$ |
|  |                     | $V_{DS} = 640\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ °C}$  | -    | -    | 500       |               |
| Drain-Source On-State Resistance               | $R_{DS(on)}$        | $V_{GS} = 10\text{ V}, I_D = 3.7\text{ A}^b$   | -    | 1.2  | -         | $\Omega$      |
| Forward Transconductance                       | $g_{fs}$            | $V_{DS} = 100\text{ V}, I_D = 3.7\text{ A}^b$  | 5.6  | -    | -         | S             |
| <b>Dynamic</b>                                 |                     |  |      |      |           |               |
| Input Capacitance                              | $C_{iss}$           | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$ , see fig. 5   | -    | 3100 | -         | pF            |
| Output Capacitance                             | $C_{oss}$           |  | -    | 800  | -         |               |
| Reverse Transfer Capacitance                   | $C_{riss}$          |  | -    | 490  | -         |               |
| Total Gate Charge                              | $Q_g$               | $V_{GS} = 10\text{ V}, I_D = 3.8\text{ A}, V_{DS} = 400\text{ V}$ , see fig. 6 and 13 <sup>b</sup>   | -    | -    | 200       | nC            |
| Gate-Source Charge                             | $Q_{gs}$            |  | -    | -    | 24        |               |
| Gate-Drain Charge                              | $Q_{gd}$            |  | -    | -    | 110       |               |
| Turn-On Delay Time                             | $t_{d(on)}$         | $V_{DD} = 400\text{ V}, I_D = 3.8\text{ A}, R_g = 6.2\text{ }\Omega, R_D = 52\text{ }\Omega$ see fig. 10 <sup>b</sup>                                  | -    | 19   | -         | ns            |
| Rise Time                                      | $t_r$               |  | -    | 38   | -         |               |
| Turn-Off Delay Time                            | $t_{d(off)}$        |  | -    | 120  | -         |               |
| Fall Time                                      | $t_f$               |  | -    | 39   | -         |               |
| Internal Drain Inductance                      | $L_D$               | Between lead, 6 mm (0.25") from package and center of die contact  | -    | 5.0  | -         | nH            |
| Internal Source Inductance                     | $L_S$               |  | -    | 13   | -         |               |
| <b>Drain-Source Body Diode Characteristics</b> |                     |  |      |      |           |               |
| Continuous Source-Drain Diode Current          | $I_S$               | MOSFET symbol showing the integral reverse p - n junction diode    | -    | -    | 5.0       | A             |
| Pulsed Diode Forward Current <sup>a</sup>      | $I_{SM}$            |  | -    | -    | 21        |               |
| Body Diode Voltage                             | $V_{SD}$            | $T_J = 25\text{ °C}, I_S = 3.8\text{ A}, V_{GS} = 0\text{ V}^b$  | -    | -    | 1.8       | V             |
| Body Diode Reverse Recovery Time               | $t_{rr}$            | $T_J = 25\text{ °C}, I_F = 3.8\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$   | -    | 650  | 980       | ns            |
| Body Diode Reverse Recovery Charge             | $Q_{rr}$            |  | -    | 3.8  | 5.7       | $\mu\text{C}$ |
| Forward Turn-On Time                           | $t_{on}$            | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )  |      |      |           |               |

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



Fig. 1 - Typical Output Characteristics,  $T_C = 25\text{ }^\circ\text{C}$



Fig. 3 - Typical Transfer Characteristics

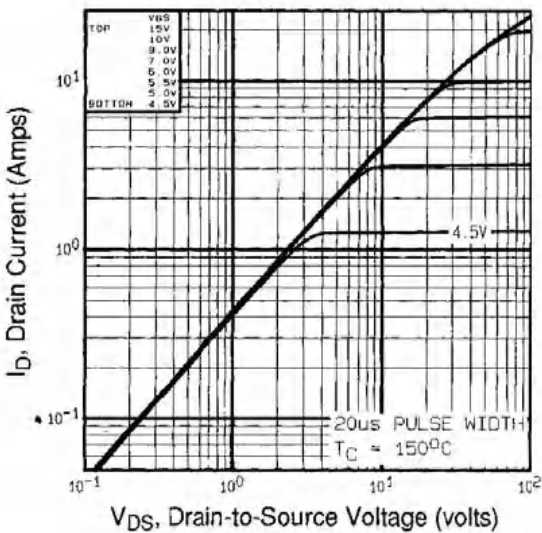


Fig. 2 - Typical Output Characteristics,  $T_C = 150\text{ }^\circ\text{C}$

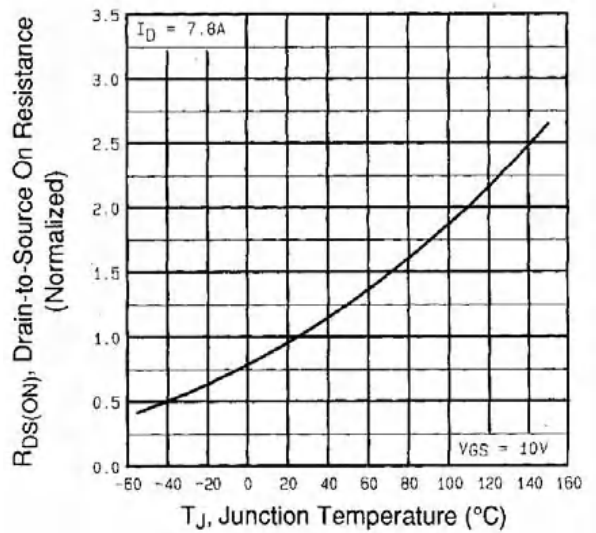


Fig. 4 - Normalized On-Resistance vs. Temperature



Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



Fig. 7 - Typical Source-Drain Diode Forward Voltage



Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



Fig. 8 - Maximum Safe Operating Area



Fig. 9 - Maximum Drain Current vs. Case Temperature

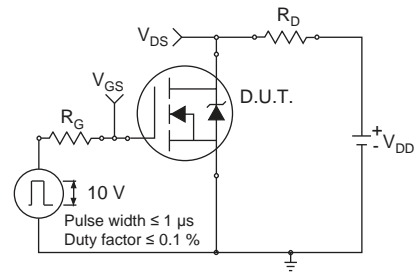


Fig. 10a - Switching Time Test Circuit

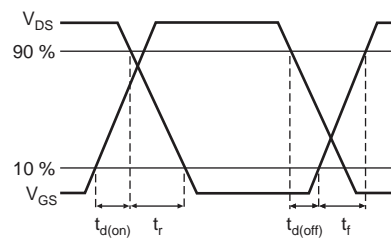


Fig. 10b - Switching Time Waveforms



Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

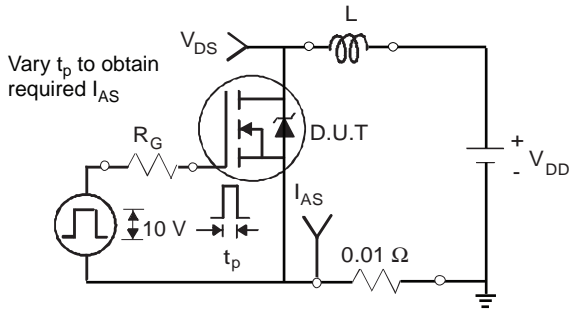


Fig. 12a - Unclamped Inductive Test Circuit



Fig. 12b - Unclamped Inductive Waveforms



Fig. 12c - Maximum Avalanche Energy vs. Drain Current



Fig. 13a - Basic Gate Charge Waveform

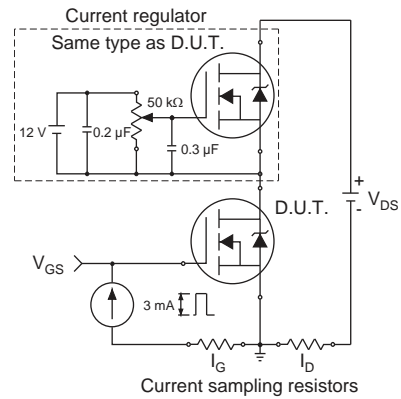
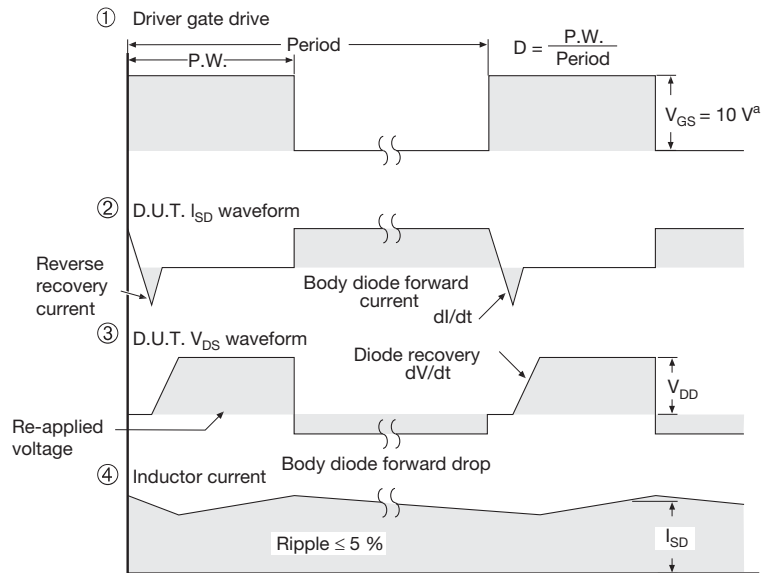
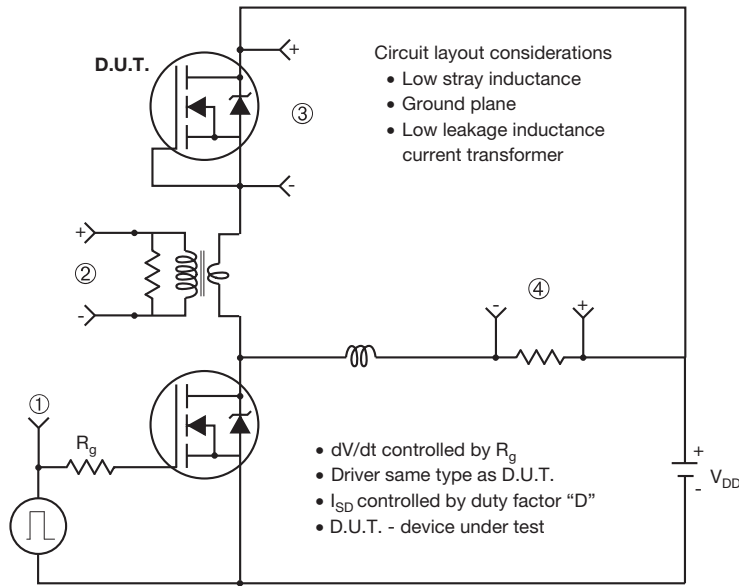


Fig. 13b - Gate Charge Test Circuit

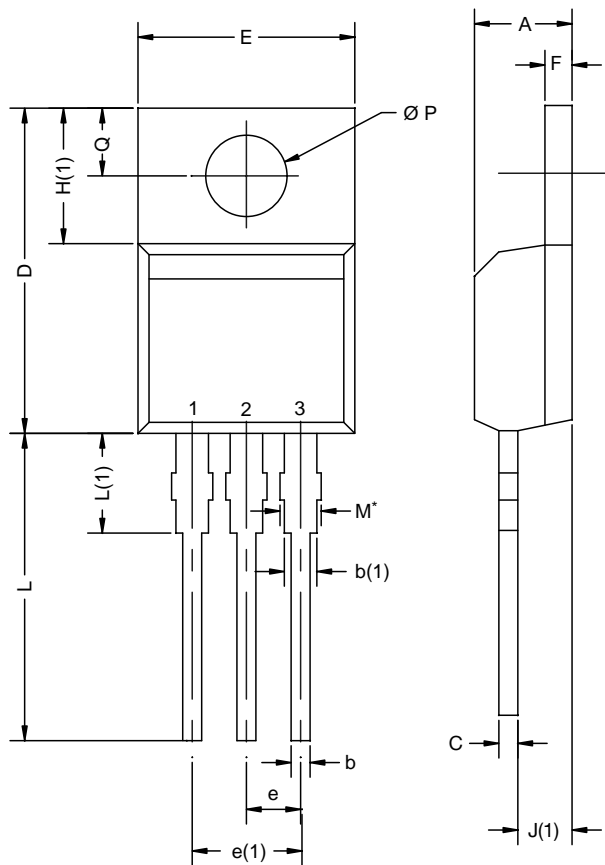
**Peak Diode Recovery dV/dt Test Circuit**



**Note**  
 a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 14 - For N-Channel**

### TO-220AB



| DIM. | MILLIMETERS |       | INCHES |       |
|------|-------------|-------|--------|-------|
|      | MIN.        | MAX.  | MIN.   | MAX.  |
| A    | 4.25        | 4.65  | 0.167  | 0.183 |
| b    | 0.69        | 1.01  | 0.027  | 0.040 |
| b(1) | 1.20        | 1.73  | 0.047  | 0.068 |
| c    | 0.36        | 0.61  | 0.014  | 0.024 |
| D    | 14.85       | 15.49 | 0.585  | 0.610 |
| E    | 10.04       | 10.51 | 0.395  | 0.414 |
| e    | 2.41        | 2.67  | 0.095  | 0.105 |
| e(1) | 4.88        | 5.28  | 0.192  | 0.208 |
| F    | 1.14        | 1.40  | 0.045  | 0.055 |
| H(1) | 6.09        | 6.48  | 0.240  | 0.255 |
| J(1) | 2.41        | 2.92  | 0.095  | 0.115 |
| L    | 13.35       | 14.02 | 0.526  | 0.552 |
| L(1) | 3.32        | 3.82  | 0.131  | 0.150 |
| Ø P  | 3.54        | 3.94  | 0.139  | 0.155 |
| Q    | 2.60        | 3.00  | 0.102  | 0.118 |

ECN: X12-0208-Rev. N, 08-Oct-12  
DWG: 5471

**Notes**

\* M = 1.32 mm to 1.62 mm (dimension including protrusion)  
Heatsink hole for HVM



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